

# MR52 SIO Contact MTBF Report

by



Percept Technology Labs LLC 5320 Pennsylvania Avenue Boulder, Colorado 80303 303.444.7480 http://www.percept.com

**Revision History:** 

Version	Date	Comments	Contributors
1.0	1/6/2025	Initial draft	MB

This document is property of Percept Technology Labs LLC. All tests, test scripts and suites, test plans, procedures, data collection methods and data presentations are property of Percept Technology Labs LLC. The testing data referenced in this document was performed in a controlled environment using specific systems and data sets, and represent results related to the specific items tested. Actual results in other environments may vary. These results do not constitute a guarantee of performance. The information in this document is provided "As Is" without any warranty of any kind.

## Approved:

Percept Technology Labs LLC shall have no liability of any kind to person or property, including special or consequential damages, resulting from Percept Technology Labs LLC providing the services covered by this report.

Project Manager: Marty Best	2/14/2025

## **TABLE OF CONTENTS**

1	INTR	ODUCTION	4
	1.1 1.2 1.3 1.4 1.5 1.6 1.7	OVERVIEW SCOPE DEFINITIONS COMPANY RESTRICTED INFORMATION REFERENCE DOCUMENTS CLIENT INFORMATION TEST ENTRANCE CRITERIA TEST EXIT CRITERIA	4 4 4 5 5 5
2	ANAL	_YSIS	
	2.1 2.2	GENERAL RELIABILITY PREDICTION ASSUMPTIONS	
3	RESU	JLTS:	7
4	APPE	ENDIX A — COMPONENT DETAIL TABLES	8
	4.1	MR52 SIO	8
5	APPE	ENDIX B — MTBF INPUT FACTORS1	2
	5.1 5.2 5.3 5.4 5.5 5.6	FAILURE RATE       12         TEMPERATURE FACTOR       12         ELECTRICAL STRESS FACTOR       12         QUALITY FACTOR       13         ENVIRONMENTAL CONDITION FACTOR       14         DEFINITION OF FAILURE       15	2 2 3 4
		TABLE OF Tables	
		MR52 SIO RELIABILITY PREDICTION	
		MR52 SIO PREDICTION VS. TEMPERATURE	
TΑ	BLE 3: N	MR52 SIO SYSTEM RELIABILITY @ AMBIENT TEMP = 25°C	8

## 1 Introduction

## 1.1 Overview

Failure rates were determined for the components in the Bill of Materials provided by HID Global. The BOM was PCA-00998 MR52-S3C. A Mean Time Between Failure (MTBF) calculation was then performed using Telcordia SR332, Issue 4, ARPP Version 12.1a, 2017.

## 1.2 Scope

This report, prepared by Percept Technology Labs LLC, documents the failure rate analysis and the results of the calculation.

#### 1.3 Definitions

BOM = Bill of Materials

FR = Failure Rate - units are failures/million hours

FIT = Failures in Time - units are failures/billion hours

MTBF = Mean Time Between Failure - units are hours

The predicted elapsed time between inherent failures of a system during operation is called the mean time between failures (MTBF). This is calculated as the arithmetic mean (average) time between failures of a system. The MTBF is typically part of a model that assumes the failed system is immediately repaired (zero elapsed time), as a part of a renewal process. In contrast, the mean time to failure (MTTF), measures average time between failures with the modeling assumption that the failed system is not repaired.

The definition of MTBF depends on the definition of what is considered a system failure. For complex, repairable systems, failures are considered to be those out of design conditions which place the system out of service and into a state for repair. Failures which occur that can be left or maintained in an unrepaired condition, and do not place the system out of service, are not considered failures under this definition. In addition, units that are taken down for routine scheduled maintenance or inventory control are not considered within the definition of failure.

For the purposes of this report, we are using the first definition of failure: that which places the system out of service and in need of repair.

## 1.4 Company Restricted Information

This document contains confidential and restricted information. Reproduction of this document outside of HID Global or Percept Technology Labs LLC is prohibited.

#### 1.5 Reference Documents

Reference documents for this evaluation included the HID Global PCA-00998 MR52-S3C Bill of Materials and component specifications.

HID Global MR52 SIO MTBF Report	Percept Technology Labs LLC	Page 4 of 15
v1.0.docx	Duplication Prohibited © 2025	Fage 4 of 18

## 1.6 Client Information

HID GLOBAL Unit 3, Cae Gwyrdd Green Meadow Springs Business Park CF15 7AB Cardiff United Kingdom

## 1.7 Test Entrance Criteria

- All necessary product-related materials and support documentation required for Percept Technology Labs LLC to execute this project.
- Access to a technical resource (person) for operational questions.

## 1.8 Test Exit Criteria

- All data collected for specified test cases.
- Completed Test Report (This document).

## 2 Analysis

## 2.1 General Reliability Prediction Assumptions

- An electronic component can only fail when current is applied.
- The probability of failure for any electronic component is constant throughout its "useful life". The probability of failure is the same from the first it is turned on until the end of its useful life is reached (usually millions of hours of run time).
- MTBF = 1/failure rate. If the failure rate number is obtained from the Telcordia database or the supplier's datasheets it has assumed 100% duty cycle. The failure rate to be used in the MTBF prediction calculation is equal to the base failure rate times the duty cycle.
- Mechanical and electrical wearout are not part of the reliability prediction calculations.

## 2.2 Environmental Stress Factors

- Ambient temperature = 25°C.
- Electrical Stress is assumed to be 50% for all components.
- Component Quality Level 1 is used for the prediction.
- The Environment is assumed to be Ground, Fixed, Uncontrolled for all components
- The assumed Duty Cycle is 100% for all components.

## 3 Results:

Table 1: MR52 SIO Reliability Prediction

P/N	Quantity	Description	FIT
	1	MR52 SIO	469.707
	Fa	ilures per Billion Hours	469.707
		MTBF	2,128,986

## **Assumptions:**

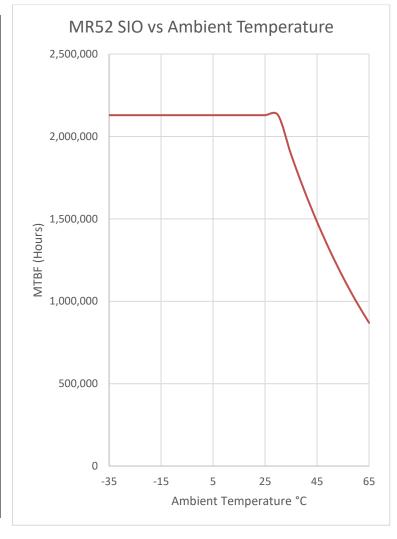
Part Stress Level = 50%

Ambient Temperature = 25°C

**Environment = "Ground Fixed, Uncontrolled"** 

Table 2: MR52 SIO Prediction vs. Temperature

MR52 SIO MTBF vs					
Temperature					
Ambient	FIT	MTBF			
-35	469.700	2,129,019			
-30	469.700	2,129,019			
-25	469.700	2,129,019			
-20	469.700	2,129,019			
-15	469.700	2,129,019			
-10	469.700	2,129,019			
-5	469.700	2,129,019			
0	469.700	2,129,019			
5	469.700	2,129,019			
10	469.700	2,129,019			
15	469.700	2,129,019			
20	469.700	2,129,019			
25	469.700	2,129,019			
30	469.700	2,129,019			
35	528.900	1,890,717			
40	596.700	1,675,884			
45	675.000	1,481,481			
50	766.200	1,305,142			
55	873.100	1,145,344			
60	999.600	1,000,400			
65	1150.300	869,338			



# 4 Appendix A — Component Detail Tables

## 4.1 MR52 SIO

Table 3: MR52 SIO System Reliability @ Ambient Temp = 25°C

Description	Qty	Ref Design	Device Fit	System Fit
CAP CER 12PF 50V 1% COG 0402	4	C1,C2,C5,C6	0.28	1.13
CAP CER 0.1UF 10% 16V X7R 0603	14	C16,C17,C18,C19,C28,C32,C33,C38,C39,C40,C47,C91,C97,C401	0.28	3.95
CAP X5R 10UF 10% 16V 0805	10	C20,C42,C44,C45,C100,C101,C1 03,C104,C105,C107	0.28	2.82
CAP X7R 1UF 16V 10% 0603	10	C48,C49,C50,C51,C52,C53,C54, C55,C56,C57	0.28	2.82
CAP X7R .01UF 50V 10% 0805 LEAD FREE	4	C66,C98,C197,C198	0.28	1.13
CAPACITOR, CERAMIC, 10UF, 50V, 10%, X5R, 1206	4	C64,C80,C81,C82	0.28	1.13
CAP X7R 1.0UF 10% 50V 1206	4	C175,C176,C178,C180	0.28	1.13
CAP TANT 100UF 10% 10V C CASE	1	C76	2.37	2.37
CAP CER 220PF 5% 25V COG 0402	2	C177,C179	0.28	0.56
DIODE, LED CLEAR RED, 0805	20	D1,D2,D3,D4,D5,D6,D7,D8,D9, D10,D11,D12,D13,D14,D16,D17 ,D18,D19,D20,D21	0.32	6.37
DIO SW 70V BAV99LT1 TO-236AX LEAD FREE	22	D22,D23,D24,D25,D26,D27,D28 ,D29,D30,D31,D32,D33,D34,D3 5,D36,D37,D88,D89,D90,D91,D 92,D93	0.02	0.54
DIO TVS UNIDIRECTIONAL 28V DO- 214AA(SMB)	23	D38,D39,D40,D41,D42,D43,D44 ,D45,D46,D47,D48,D49,D50,D5 1,D52,D53,D54,D55,D56,D57,D 58,D59,D87	0.27	6.10
DIO TVS 12.0V SM712 SOT-23-3 LEAD FREE	3	D64,D73,D75	0.06	0.17
DIO TVS 5.0V SMBJ UNIDIRECTIONAL LEAD FREE	2	D71,D72	2.32	4.63
DIODE SCHOTTKY 40V 3.0A SMA	2	D85,D86	2.64	5.27
PTC SMT 30V 50MA FOOTPRINT:1210	2	F1,F2	1.20	2.40

HID Global MR52 SIO MTBF Report v1.0.docx	Percept Technology Labs LLC Duplication Prohibited © 2025	Page 8 of 15
V1.0.00CX	Duplication Prohibited © 2025	

Description	Qty	Ref Design	Device Fit	System Fit
PTC SMT 60V 500MA FOOTPRINT:2920	2	F4,F5	1.20	2.40
CONN HEADER STRAIGHT THRU HOLE 2.54MM 3-WAY	1	J1	0.44	0.44
CONN HEADER STRAIGHT THRU HOLE 2.54MM 2-WAY	1	J4	0.15	0.15
RLY SPDT 10A 5V SEALED SMD	6	K1,K2,K3,K4,K5,K6	33.4 5	200.68
IND WIREWOUND 47UH ±20 1.8A UNSHIELDED	2	L20,L21	0.60	1.20
FILTER FERRITE BEAD 6000HM @ 100MHZ 1A 1206	3	L3,L16,L18	0.25	0.75
XSTR PNP 40V MMBT3906 TO-236AX LEAD FREE	4	Q1,Q2,Q3,Q4	0.04	0.15
TRANSISTOR, NPN, 40V, 0.6A, SOT-23	12	Q5,Q6,Q7,Q8,Q9,Q10,Q13,Q14 ,Q15,Q16,Q17,Q18	0.04	0.46
XSTR NFET 60V SOT-23 LEAD FREE	2	Q11,Q12	0.04	0.08
RES FILM 22K 5% 0.1W 0603	12	R1,R2,R3,R4,R5,R6,R83,R84,R8 5,R86,R206,R207	0.20	2.40
RES FILM 33R 5% 0.1W 0603	5	R7,R8,R9,R10,R95	0.20	1.00
RES FILM 1K 1% 1/4W 1206	16	R11,R12,R15,R17,R19,R20,R23, R25,R27,R28,R31,R33,R35,R36, R40,R41	0.20	3.20
RES FILM 470 .125W 5% 0805 ROHS COMPLIANT	2	R13,R14	0.20	0.40
Res Thick Film 0603 1K Ohm 1% 0.1W(1/10W) ±100ppm/°C Lead Free	31	R29,R30,R63,R64,R65,R66,R67, R68,R70,R71,R94,R189,R190,R1 91,R192,R193,R194,R195,R196, R197,R198,R199,R200,R201,R2 02,R208,R209,R210,R211,R212, R213	0.20	6.19
RES FILM 10K 1% 1/4W 1206	10	R43,R44,R45,R46,R47,R48,R49, R50,R62,R504	0.20	2.00
RES FILM 10K OHM 0.100W (1/10W) 5% 0603 ROHS COMPLIANT	10	R51,R52,R53,R54,R55,R56,R57, R58,R1101,R1102	0.20	2.00
Res Thick Film 0603 120 Ohm 5% 0.1W(1/10W) ±200ppm/°C Lead Free	1	R61	0.20	0.20
RES FILM 2.2K 5% 0.1W 0603	4	R79,R80,R81,R82	0.20	0.80
RES FILM 0.0 0.1W (1/10W) 5% 0603 ROHS COMPLIANT	2	R87,R111	0.20	0.40

HID Global MR52 SIO MTBF Report	Percept Technology Labs LLC	Page 9 of 15
v1.0.docx	Duplication Prohibited © 2025	Fage 9 01 13

Description	Qty	Ref Design	Device Fit	System Fit
RES THICK FILM 931 0.1W 1% 0603, LEAD FREE	1	R88	0.20	0.20
RES 1.5K 0402 1% 1/16W	1	R90	0.20	0.20
RES FILM 0 OHM 0.25W 1206	1	R129	0.20	0.20
RES FILM 68K 0.063W 1% 0402	2	R130,R132	0.20	0.40
RES FILM 13.0K OHM 0.063W (1/16W) 1% 0402 ROHS COMPLIANT	1	R131	0.20	0.20
RES FILM 4.7K .063W 1% 0402 LEAD FREE	1	R133	0.20	0.20
RES FILM 4.7K 5% ±200PPM/°C 1/10W 0603	37	R134,R135,R136,R137,R138,R1 39,R140,R141,R149,R150,R151, R162,R163,R164,R165,R166,R1 67,R168,R169,R170,R171,R172, R173,R174,R175,R176,R177,R1 78,R179,R180,R181,R182,R183, R184,R185,R186,R187	0.20	7.39
RES FILM 10R 1% 1/4W 0603 ANTI-SURGE	13	R300,R301,R302,R303,R304,R4 00,R401,R800,R801,R802,R803, R804,R805	0.20	2.60
SW DIP SMT TAPE SEAL 8 POS LF-ROHS	1	S1	14.9 7	14.97
TERM HDR FOR QWK DISC 4 POS ROHS	5	TB1,TB2,TB3,TB4,TB5	0.29	1.47
TERM HDR FOR QWK DISC 5 POS ROHS	1	TB6	0.37	0.37
TERM HDR FOR QWK DISC 3 POS ROHS	1	TB7	0.22	0.22
TERM HDR FOR QWK DISC 6 POS ROHS	5	TB8,TB9,TB10,TB11,TB12	0.44	2.21
IC MICROCONTROLLER ARM STM32G0C1X CORTEX-M0+, 64MHZ, 512KB FLASH, 144K RAM, LQFP-100	1	U1	0.63	0.63
IC DUAL COMP SO8, SOIC8	3	U4,U14,U15	0.14	0.41
IC TRANSCEIVER RS485/ RS422 HALF DUPLEX 8SOIC LEAD FREE	3	U5,U6,U7	0.01	0.04
IC CRYPTO ELEMENT SOIC-8	1	U9	0.16	0.16
IC LINEAR VOLT REG, +3.3V, 3A, TO263/DDPAK/D2PAK/SOT404	1	U13	0.39	0.39
IC REG SWITCHING 1.2-12V 2A 300KHZ SOP-FD-8	2	U32,U33	1.03	2.07
XTAL 8.0MHZ, 30PPM, -40 TO +85 DEG, 3225, (X4 PAD) SMD	1	Y1	5.70	5.70

HID Global MR52 SIO MTBF Report v1.0.docx	Percept Technology Labs LLC Duplication Prohibited © 2025	Page 10 of 15
V1.0.000X	Duplication i Tonibited @ 2020	

Description	Qty	Ref Design	Device Fit	System Fit
OSC XTAL 32.7680KHZ ±20PPM -40°C - +85°C SMD 3.2X1.5MM	1	Y2	5.70	5.70

Total FIT	313.138
<b>Environmental Factor</b>	1.500
System Duty Cycle	100%
System FIT	469.707
System MTBF	2,128,986

## 5 Appendix B — MTBF Input Factors

#### 5.1 Failure Rate

 $\lambda = \lambda b * \pi 1 * \pi 2 * \pi 3 * \pi 4$ 

where

 $\lambda$  = failure rate

 $\lambda b$  = base failure rate

 $\pi t$  = operating temperature factor

 $\pi es$  = electrical stress factor

 $\pi q$  = quality factor

 $\pi ec$  = environmental condition factor

## **5.2 Temperature Factor**

The prediction process uses a Temperature Factor to model the effect of temperature on failure rate. The value of this factor is based on the device operating temperature and the type of device. The value is normalized to a temperature of 40°C, which produces a Temperature Factor of 1.0 for all device types. When actual device operating temperature differs from the normalized temperature, the actual device operating temperature may be used. In general, temperatures less than 40°C result in a factor less than 1 and temperatures greater than 40°C result in factors greater than 1. The prediction program contains temperature models for each component type which calculates the factor.

#### **5.3 Electrical Stress Factor**

The prediction process assumes an electrical stress percentage of 50% (electrical stress factor = 1). If the device's application produces electrical stress percentage higher or lower than this base value, then the failure rate must be adjusted using the electrical stress factor. The prediction program contains electrical stress models for each component type which calculates the factor.

Part	Electrical Stress Percentage
Capacitor	(Sum of applied dc voltage plus ac peak voltage) / (rated voltage)
Resistor, fixed	Applied power / rated power
Resistor, variable	(V2in / total resistance) / rated power
Relay, switch	Contact current / rated current
Diode, general	Average forward current / rated forward current
Diode zener	Actual zener current or power / rated current or power
Transistor	Power dissipated / rated power

HID Global MR52 SIO MTBF Report	
v1.0.docx	

## 5.4 Quality Factor

The device failure rates used for the prediction process reflect the expected field reliability performance of generic device types. The actual reliability of a specific device will vary as a function of the degree of effort and attention paid by an equipment manufacturer to factors such as device selection/application, supplier selection/control, electrical/mechanical design margins, equipment manufacture process control, and quality program requirements. The table below describes the four quality levels and presents the values for their associated Quality Factor:

Quality Level 0	This level shall be assigned to commercial-grade, reengineered, remanufactured, reworked, salvaged, or gray-market components that are procured and used without device qualification, lot-to-lot controls, or an effective feedback and corrective action program by the primary equipment manufacturer or its outsourced lower-level design or manufacturing subcontractors. However, steps must have been taken to ensure that the components are compatible with the design application.  Quality Factor = 6		
Quality Level 1	This level shall be assigned to commercial-grade components that are procured and used without thorough device qualification or lot-to-lot controls by the equipment manufacturer. However,		
	(a) steps must have been taken to ensure that the components are compatible with the design application and manufacturing process; and		
	(b) an effective feedback and corrective action program must be in place to identify and resolve problems quickly in manufacture and in the field.		
	Quality Factor = 3		
Quality Level 2	This level shall be assigned to components that meet requirements (a) and (b) of Quality Level 1, plus the following:		
	(c) purchase specifications must explicitly identify important characteristics (electrical, mechanical, thermal, and environmental) and acceptable quality levels (i.e. AQLs, Defects per Million, etc) for lot control;		
	(d) devices and device manufacturers must be qualified and identified on approved parts/manufacture's lists (device qualification must include appropriate life and endurance tests);		
	(e) lot-to-lot controls, either by the equipment manufacturer or the device manufacturer, must be in place at adequate AQLs/DPMs to ensure consistent quality.		
	Quality Factor = 1		
Quality Level 3	This level shall be assigned to components that meet requirements (a) thru (e) of Quality Levels 1 and 2 plus the following:		
	(f) device families must be re-qualified periodically;		
	(g) lot-to-lot controls must include early life reliability control of 100% screening (temperature cycling and burn-in), which, if the results warrant it, may be reduced to a "reliability audit" (i.e. a sample basis) or to an acceptable "reliability monitor" with demonstrated and accepted cumulative early failure values of less than 200ppm out to 10,000 hours;		
	(h) where burn-in screening is used, the Percent Defective Allowed (PDA) shall be specified and shall not exceed 2% and		
	(i) and ongoing, continuous reliability improvement program must be implemented by both the device and equipment manufacturers.		
	Quality Factor = .8		
	·		

HID Global MR52 SIO MTB	F Report
v1.0.docx	

## 5.5 Environmental Condition Factor

The prediction process defines 6 environmental conditions. A separate prediction should be made for each environmental condition to which the equipment may be exposed. The prediction process uses and Environment Factor as a quantitative expression for a condition's effect on failure rate The factor goes from 1 (ground-based, fixed, controlled environment) to 15 (for a space based commercial environment such as a commercial communication satellite).

Environment	Factor	Nominal Environmental Conditions
Ground, Fixed, Controlled	1	Vibration/shock stresses: Low Atmospheric variations: Low Temp cycling stresses: Low Application examples: Central offices, data center, environmentally controlled vaults, environmentally controlled remote shelters, and environmentally controlled customer premise areas.
Ground, Fixed, Uncontrolled (limited)	1.5	Vibration/shock stresses: Low to moderate Atmospheric variations: Low to moderate Temp cycling stresses: Moderate to High Application examples: Weather-protected remote terminals, outdoor equipment, and radio tower equipment.
Ground Fixed, Uncontrolled (moderate)	2.0	Vibration/shock stresses: Moderate to High Atmospheric variations: Low to moderate Temp cycling stresses: Moderate to High Application examples: Remote terminals and outdoor equipment in manholes, and near direct path of railroad, highway, and air traffic.
Ground, Mobile (both vehicular mounted and portable)	4.0	Vibration/shock stresses: Extreme Atmospheric variations: Low to moderate Temp cycling stresses: High Application examples: Equipment that can be in rapid motion relative to the ground, including cell phones and hand-held devices, portable operating equipment, and test equipment
Airborne, Commercial	6.0	Vibration/shock stresses: Extreme Atmospheric variations: High Temp cycling stresses: High Application examples: Passenger compartment of commercial aircraft
Space-based, Commercial (low earth orbit)	15.0	Vibration/shock stresses: Extreme Atmospheric variations: High Temp cycling stresses: High Application examples: Commercial satellites

HID Global MR52 SIO MTBF Report v1.0.docx	Percept Technology Labs LLC Duplication Prohibited © 2025	Page 14 of 15
V1.0.000X	Duplication Frombited @ 2023	

#### 5.6 Definition of Failure

The definition of a failure should be well understood. This is a crucial element in predicting system reliability parameters.

The following is not included in failure rate predictions:

- Manufacturing process-induced errors.
- Software failures.
- Failures from procedural errors.

Failures in systems with multiple functions may be hard to define. In complex equipment, it may be useful to distinguish between failures affecting maintenance or repair and those affecting service. For example, the failure of an LED is likely to cause a return, but may not cause a service outage. Consequently, LEDs should be included in the failure rate estimate when the estimate is used to determine return rates, but they could likely be disregarded if the estimate is used to determine service availability.